

## **SS8550**

# **2W Output Amplifier of Portable Radios in Class B Push-pull Operation.**

- Complimentary to SS8050
- Collector Current: I<sub>C</sub>=1.5A
- Collector Power Dissipation: P<sub>C</sub>=2W (T<sub>C</sub>=25°C)



1. Emitter 2. Base 3. Collector

## **PNP Epitaxial Silicon Transistor**

## **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V <sub>CBO</sub>	Collector-Base Voltage	-40	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-25	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V	
I <sub>C</sub>	Collector Current	-1.5	Α	
P <sub>C</sub>	Collector Power Dissipation	1	W	
T <sub>J</sub>	Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature	-65 ~ 150	°C	

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub> Collector-Base Breakdown Voltage I <sub>C</sub>		$I_C = -100 \mu A, I_E = 0$	-40			V
		$I_C = -2mA$ , $I_B = 0$	-25			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = -100 \mu A, I_C = 0$	-6			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = -35V, I_{E} = 0$			-100	nA
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = -6V, I <sub>C</sub> =0			-100	nA
h <sub>FE1</sub> h <sub>FE2</sub> h <sub>FE3</sub>	DC Current Gain	V <sub>CE</sub> = -1V, I <sub>C</sub> = -5mA V <sub>CE</sub> = -1V, I <sub>C</sub> = -100mA V <sub>CE</sub> = -1V, I <sub>C</sub> = -800mA	45 85 40	170 160 80	300	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -800mA, I <sub>B</sub> = -80mA		-0.28	-0.5	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = -800mA, I <sub>B</sub> = -80mA		-0.98	-1.2	V
V <sub>BE</sub> (on)	Base-Emitter on Voltage	$V_{CE}$ = -1V, $I_{C}$ = -10mA		-0.66	-1.0	V
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = -10V, I <sub>E</sub> =0 f=1MHz		15		pF
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = -10V, I <sub>C</sub> = -50mA	100	200		MHz

## **h**<sub>FE</sub>Classification

· <del>-</del>				
	Classification	В	С	D
	h <sub>FE2</sub>	85 ~ 160	120 ~ 200	160 ~ 300

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## **Typical Characteristics**

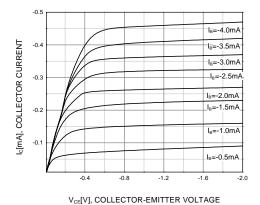


Figure 1. Static Characteristic

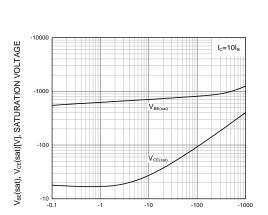


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

I<sub>c</sub>[mA], COLLECTOR CURRENT

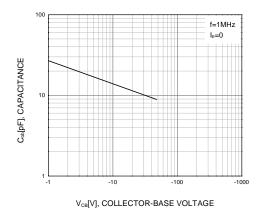


Figure 5. Collector Output Capacitance

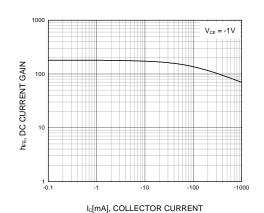


Figure 2. DC current Gain

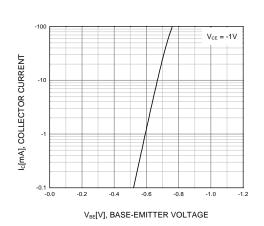


Figure 4. Base-Emitter On Voltage

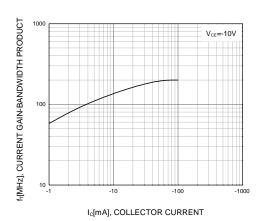
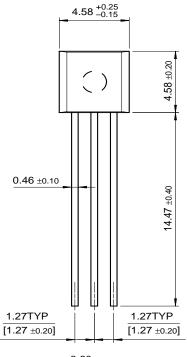


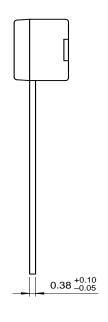
Figure 6. Current Gain Bandwidth Product

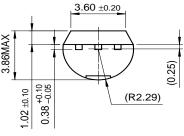
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## **Package Dimensions**

TO-92







Dimensions in Millimeters

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CROSSVOLT™	FRFET™	MicroPak™	QFET™	SuperSOT™-8
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EnSigna™	I <sup>2</sup> C <sup>TM</sup>	$OCX^{TM}$	RapidConfigure™	UHC™
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